

REMARKS/ARGUMENTS

The Applicant has carefully considered this application in connection with the Examiner's Action and respectfully requests reconsideration of this application in view of the following remarks.

The Applicant originally submitted Claims 1-20 in the application. Presently, the Applicant has neither amended, canceled nor added any claims. Accordingly, Claims 1-20 are currently pending in the application.

I. Rejection of Claims 1-8, 10-18 and 20 under 35 U.S.C. §102

The Examiner has rejected Claims 1-8, 10-18 and 20 under 35 U.S.C. §102(b) as being anticipated by U.S. Patent No. 5,841,166 to D'Anna, *et al.* ("D'Anna"). Independent Claims 1 and 11 currently include the element of forming a lightly-doped source/drain region with only a first dopant, the light-doped source/drain regions being formed between first and second isolation structures. D'Anna fails to disclose this element.

D'Anna is directed to a lateral DMOS transistor for RF/microwave applications. (Title). D'Anna teaches that an N-drift region **46** is formed within a P-epi layer **42**. D'Anna then teaches that an active area mask is formed to define where the field oxides **52** will be present, and that the field oxides **52** are then grown to a thickness of 0.5 to 3 microns. (See, D'Anna at column 2, lines 55-65). Accordingly, D'Anna teaches first forming its N-drift region **46** and then forming its field oxides **52**, wherein Claims 1 and 11 currently require forming a lightly-doped source/drain region with only a first dopant, the light-doped source/drain regions being formed between first and second isolation

structures. Thus, D'Anna fails to disclose the element of forming lightly-doped source/drain regions between already existing first and second isolation structures.

The Examiner is attempting to argue that no order is implied within the claims. More specifically, the Examiner is attempting to argue that the language "the lightly-doped source/drain region formed between first and second isolation structures" does not imply an order. The Applicant respectfully disagrees. Namely, for the lightly-doped source/drain region to be formed between the first and second isolation structures, the first and second isolation structures must be already present. Had the claims recited that the lightly-doped source/drain region is "located" between the first and second isolation structures, as was the claim language before being amended following the first Examiner's Action, the Examiner's argument would be more believable. However, the pending claims require that the lightly-doped source/drain region be "formed" between the first and isolation structures, as opposed to "located" therebetween. Thus, an order is present.

Therefore, D'Anna does not disclose each and every element of the claimed invention and as such, is not an anticipating reference. Because Claims 2-8, 10, 12-18 and 20 are dependent upon Claims 1 and 11, D'Anna also cannot be an anticipating reference for Claims 2-8, 10, 12-18 and 20. Accordingly, the Applicant respectfully requests the Examiner to withdraw the §102 rejection with respect to these Claims.

II. Rejection of Claims 1-3 and 11-13 under 35 U.S.C. §102

The Examiner has rejected Claims 1-3 and 11-13 under 35 U.S.C. §102(b) as being anticipated by U.S. Patent No. 4,918,026 to Kosiak, *et al.* ("Kosiak"). Independent Claims 1 and 11

currently include the element of forming a lightly-doped source/drain region with only a first dopant, the light-doped source/drain regions being formed between first and second isolation structures. Kosiak fails to disclose this element.

Kosiak is directed to a process for forming vertical bipolar transistor and high voltage CMOS in a single integrated circuit chip. (Title). Kosiak teaches that lightly doped n-type wells **114**, **214**, and **314** are formed within a substrate **12**. (See, Kosiak at column 4, lines 39-45, and the associated FIG. 2B). Kosiak then teaches that many other processing steps are performed before forming field oxide regions **50**, **120**, **220**, **320**, and **322** to isolate various different features of the monocrystalline silicon chip **10**. (See, Kosiak at column 5, lines 40-55, and the associated FIG. 2E).

Accordingly, Kosiak teaches first forming its lightly doped n-type wells **114**, **214**, and **314** and then forming its field oxide regions **50**, **120**, **220**, **320**, and **322**, wherein Claims 1 and 11 currently require forming its lightly-doped source/drain regions between first and second isolation structures. Thus, Kosiak fails to disclose the element of forming lightly-doped source/drain regions between already existing first and second isolation structures. As previously indicated, this order is present in the independent Claims.

Therefore, Kosiak does not disclose each and every element of the claimed invention and as such, is not an anticipating reference. Because Claims 2-3 and 12-13 are dependent upon Claims 1 and 11, Kosiak also cannot be an anticipating reference for Claims 2-3 and 12-13. Accordingly, the Applicant respectfully requests the Examiner to withdraw the §102 rejection with respect to these Claims.

III. Rejection of Claims 9 and 19 under 35 U.S.C. §103

The Examiner has rejected Claims 9 and 19 under 35 U.S.C. §103(a) as being unpatentable over D'Anna. As presented above, independent Claims 1 and 11 currently include the element of forming a lightly-doped source/drain region with only a first dopant, the light-doped source/drain regions being formed between first and second isolation structures. As established above, D'Anna fails to disclose this element. D'Anna further fails to suggest this element. Among other reasons, D'Anna fails to disclose this element because D'Anna specifically requires that its field oxides **52** be formed after its N-drift region **46**. Moreover, one skilled in the art, given the detailed teachings of D'Anna, would not be motivated by the teachings of D'Anna to form its field oxides **52** prior to forming its N-drift region **46**. Therefore, D'Anna fails to both teach and suggest the claimed element of forming a lightly-doped source/drain region with only a first dopant, the light-doped source/drain regions being formed between first and second isolation structures.

Thus, D'Anna fails to teach or suggest the invention recited in independent Claims 1 and 11 and their dependent claims, when considered as a whole. Accordingly, D'Anna fails to establish a prima facie case of obviousness with respect to these claims. Claims 9 and 19 are therefore not obvious in view of D'Anna.

In view of the foregoing remarks, the cited reference does not support the Examiner's rejection of Claims 9 and 19 under 35 U.S.C. §103(a). The Applicant therefore respectfully requests the Examiner withdraw the rejection.


IV. Conclusion

In view of the foregoing amendment and remarks, the Applicant now sees all of the Claims currently pending in this application to be in condition for allowance and therefore earnestly solicits a Notice of Allowance for Claims 1-20.

The Applicant requests the Examiner to telephone the undersigned attorney of record at (972) 480-8800 if such would further or expedite the prosecution of the present application. The Commissioner is hereby authorized to charge any fees, credits or overpayments to Deposit Account 08-2395.

Respectfully submitted,

HITT GAINES, PC



Greg H. Parker
Registration No. 44,995

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P.O. Box 832570
Richardson, Texas 75083
(972) 480-8800